

N-channel 30 V 2.95 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 2 — 15 June 2012

Product data sheet

Ultra low QG, QGD, & QOSS for high system efficiencies at low and high

Synchronous buck regulator

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

loads

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology

1.3 Applications

- DC-to-DC converters
- Load switching

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u> -	-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	91	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u>	-	3.3	3.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u>	-	2.45	2.95	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 4.5 V; I _D = 25 A; V _{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.4	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I _D = 25 A; V_{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.7	-	nC

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT1210 (LFPAK33)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PSMN2R9-30MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210		

4. Limiting values

Table 4. Limiting values

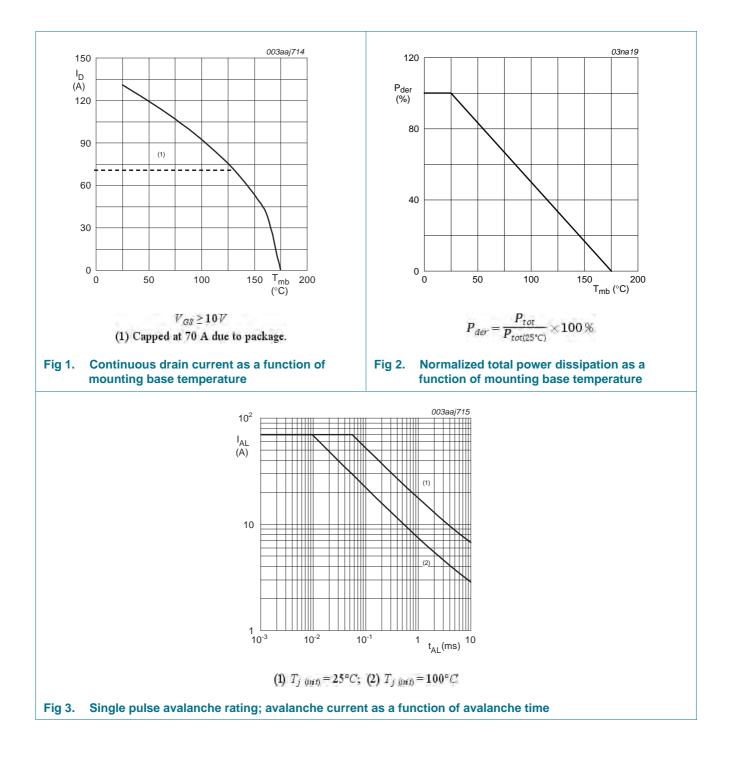
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C	-	30	V
V _{GS}	gate-source voltage		-20	20	V
ID	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	А
		V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> -	70	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 4</u>	-	523	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	91	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	340	-	V
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	70	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	523	А
Avalanche rug	gedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 70 \text{ A}; \\ V_{sup} \leq 30 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \text{ unclamped}; \\ see \underline{\text{Figure 3}} $	-	75	mJ

[1] Continuous current is limited by package.

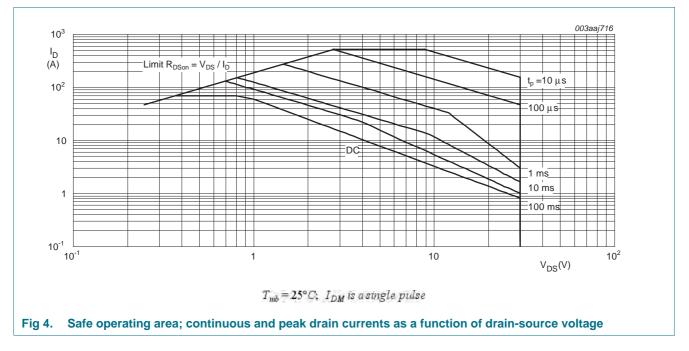
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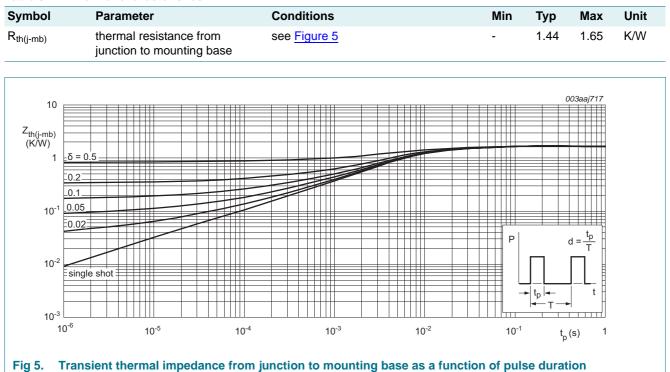
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5. Thermal characteristics

Table 5.Thermal characteristics



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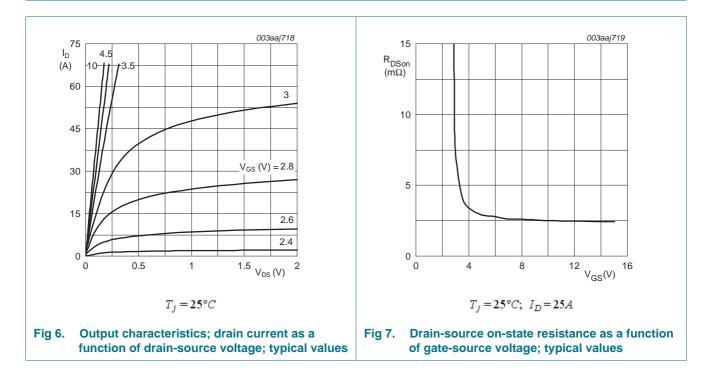
6. Characteristics

	haracteristics			-		
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static charac	cteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.45	1.78	2.15	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature		-	-4.3	-	mV/K
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u>	-	3.3	3.8	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; see <u>Figure 11</u> ; see <u>Figure 10</u>	-	-	6.5	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 10</u>	-	2.45	2.95	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	- 5.05	mΩ	
R _G	gate resistance	f = 1 MHz	1.23	2.46	4.92	Ω
Dynamic cha	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 12; see Figure 13	-	36.1	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	16.7	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	34.8	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V;	-	6.1	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3.9	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.2	-	nC
Q _{GD}	gate-drain charge		-	4.4	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; \text{ see } \frac{\text{Figure } 12;}{\text{see } \frac{\text{Figure } 13}{12}}$	-	2.7	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	2419	-	pF
	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	500	-	pF
Coss						

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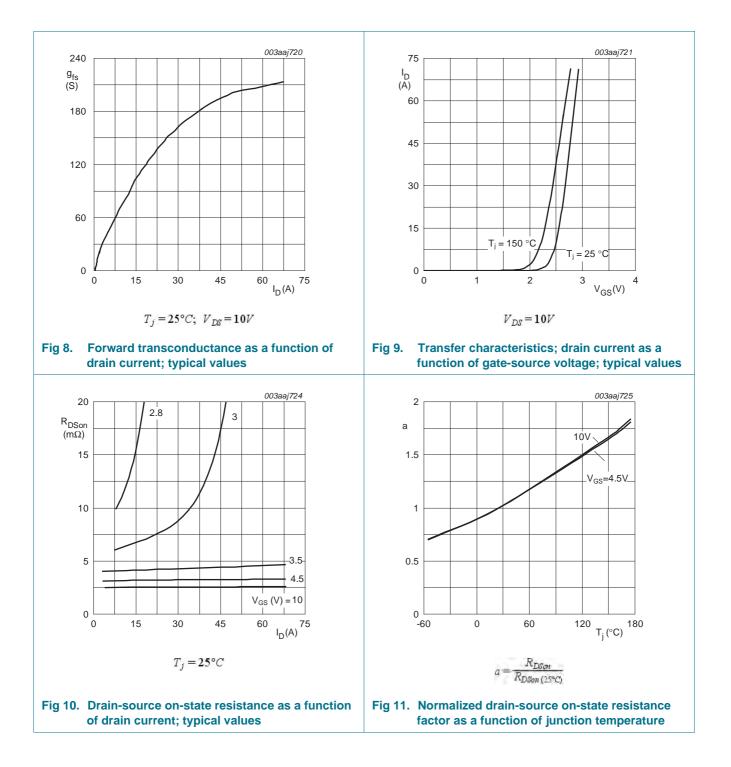
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_L = 0.6 Ω ; V_{GS} = 4.5 V;	-	17.7	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	30.8	-	ns
t _{d(off)}	turn-off delay time		-	24.6	-	ns
t _f	fall time		-	19.3	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ T _j = 25 °C	-	15.1	-	nC
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.82	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	21.8	-	ns
Qr	recovered charge	V _{DS} = 15 V	-	15.6	-	nC
t _a	reverse recovery rise time	V _{GS} = 0 V; I _S = 25 A; dI _S /dt = -100 A/µs; V _{DS} = 15 V; see <u>Figure 16</u>	-	12.9	-	ns
t _b	reverse recovery fall time		-	8.9	-	ns



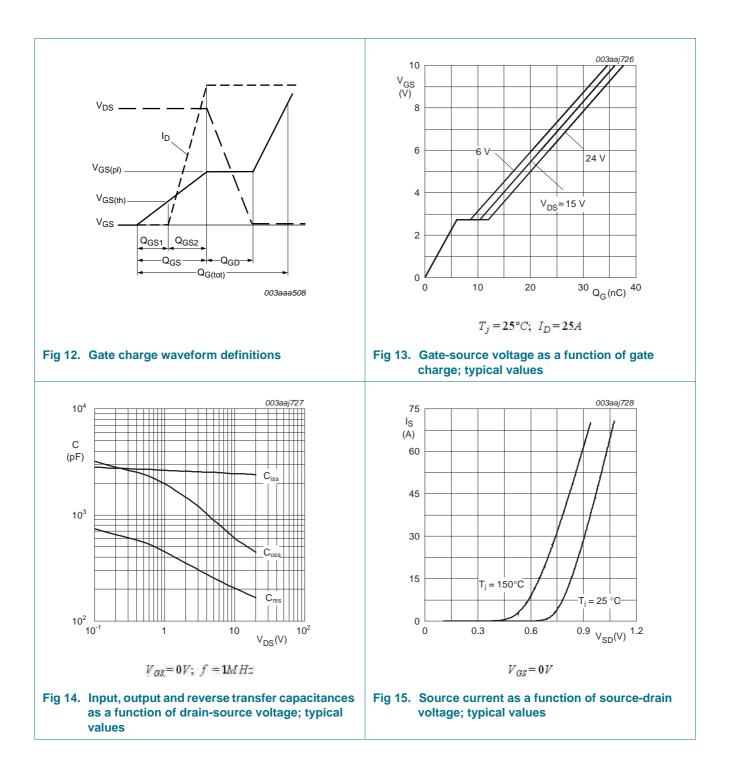
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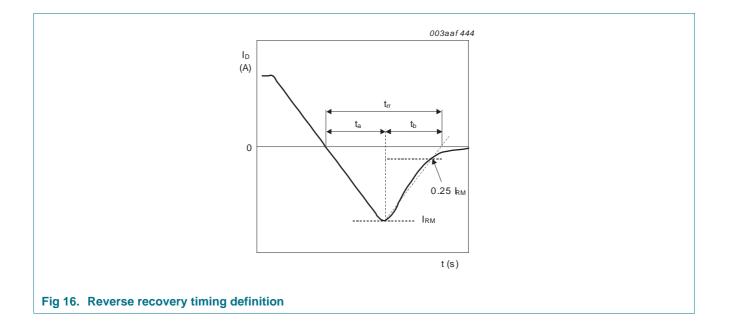
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7. Package outline

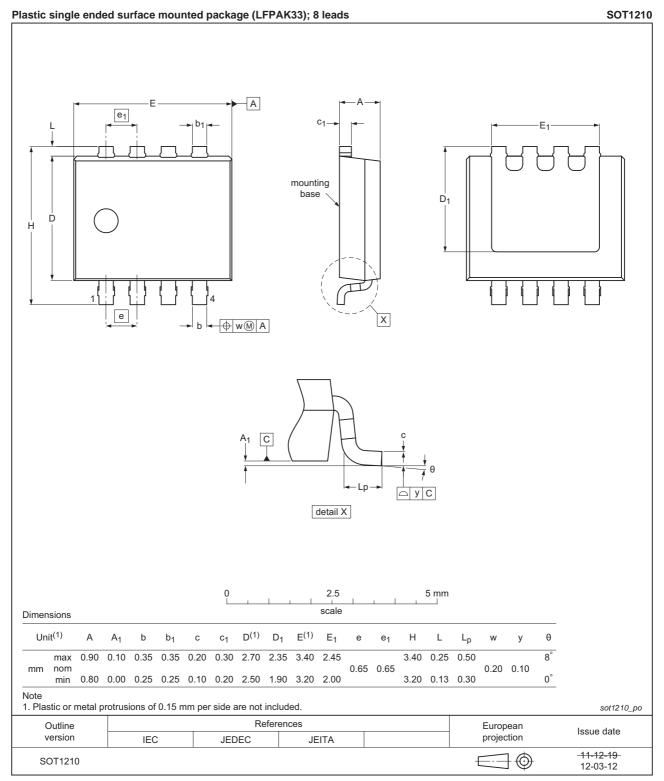


Fig 17. Package outline SOT1210 (LFPAK33)

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8. Revision history

Table 7.Revision hi	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R9-30MLC v.2	20120615	Product data sheet	-	PSMN2R9-30MLC v.1

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9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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PSMN2R9-30MLC

N-channel 30 V 2.95 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13